

Title (en)

MOSFET device formed in epitaxial layer

Title (de)

In einer Epitaxialschicht ausgebildetes MOSFET-Bauteil

Title (fr)

Dispositif MOSFET formé dans une couche épitaxiale

Publication

**EP 0716454 A2 19960612 (EN)**

Application

**EP 95118578 A 19951124**

Priority

- JP 30401894 A 19941207
- JP 8231595 A 19950407

Abstract (en)

Over a well region 3a, 3b formed over a semiconductor substrate body, there is formed an epitaxial layer 2E which has a lower impurity concentration than the well region. MOSFETs are mounted on the epitaxial layer. A field insulating film 4 is extended in a depth-wise direction to contact with the well region. The MOSFETs have their source/drain regions formed in the epitaxial layer to form a punch-through stopper layer 5N3, 5P3 between the sources and drains. <IMAGE>

IPC 1-7

**H01L 29/10**; **H01L 29/78**; **H01L 27/092**

IPC 8 full level

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CPC (source: EP)

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Cited by

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DOCDB simple family (publication)

**EP 0716454 A2 19960612**; **EP 0716454 A3 19990929**; CN 1092402 C 20021009; CN 1133494 A 19961016; CN 1323058 A 20011121; CN 1323063 A 20011121; JP H08213478 A 19960820; SG 70082 A1 20000125

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